N-Channel Silicon MOSFET



2SK2682LS

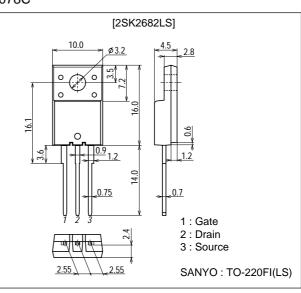
Ultrahigh-Speed Switching Applications

Features

- Low ON-resistance.
- High-speed diode.
- Micaless package facilitating mounting.

Package Dimensions

unit : mm 2078C



Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	VDSS		250	V
Gate-to-Source Voltage	VGSS		±30	V
Drain Current (DC)	۱D		13	А
Drain Current (Pulse)	IDP	PW≤10µs, duty cycle≤1%	52	А
Allowable Power Dissipation	PD		2	W
		Tc=25°C	35	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Unit
Drain-to-Source Breakdown Voltage	V(BR)DSS	ID=1mA, VGS=0	250			V
Gate-to-Source Breakdown Voltage	V(BR)GSS	IG=±100μA, VGS=0	±30			V
Zero-Gate Voltage Drain Current	IDSS	V _{DS} =250V, V _{GS} =0			1.0	mA
Gate-to-Source Leakage Current	IGSS	VGS=±25V, VDS=0			±10	μΑ
Cutoff Voltage	VGS(off)	V _{DS} =10V, I _D =1mA	2.0		3.0	V

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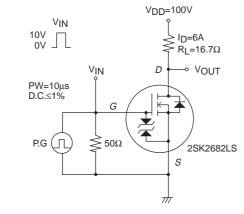
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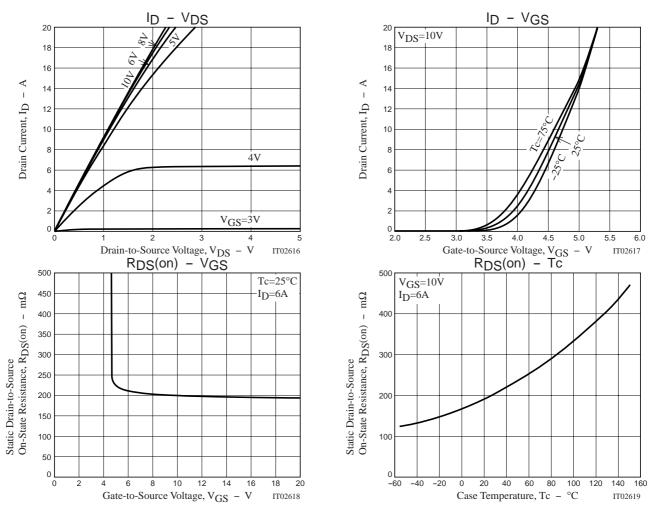
SANYO Electric Co., Ltd. Semiconductor Company TOKYO OFFICE Tokyo Bldg., 1-10, 1 Chome, Ueno, Taito-ku, TOKYO, 110-8534 JAPAN Continued from preceding page.

Parameter	Symbol	Conditions	Ratings			Linit
			min	typ	max	Unit
Forward Transfer Admittance	yfs	V _{DS} =10V, I _D =6A	6	10		S
Static Drain-to-Source On-State Resistance	R _{DS} (on)	ID=6A, VGS=10V		200	270	mΩ
Input Capacitance	Ciss	V _{DS} =20V, f=1MHz		1290		pF
Output Capacitance	Coss	V _{DS} =20V, f=1MHz		300		pF
Reverse Transfer Capacitance	Crss	V _{DS} =20V, f=1MHz		125		pF
Turn-ON Delay Time	td(on)	See specified Test Circuit.		22		ns
Rise Time	tr	See specified Test Circuit.		66		ns
Turn-OFF Delay Time	t _d (off)	See specified Test Circuit.		320		ns
Fall Time	tf	See specified Test Circuit.		105		ns
Diode Forward Voltage	VSD	IS=12A, VGS=0		1.0	1.5	V
Diode Reverse Recovery Time	t _{rr}	IS=12A, di/dt=100A/µs		160		ns

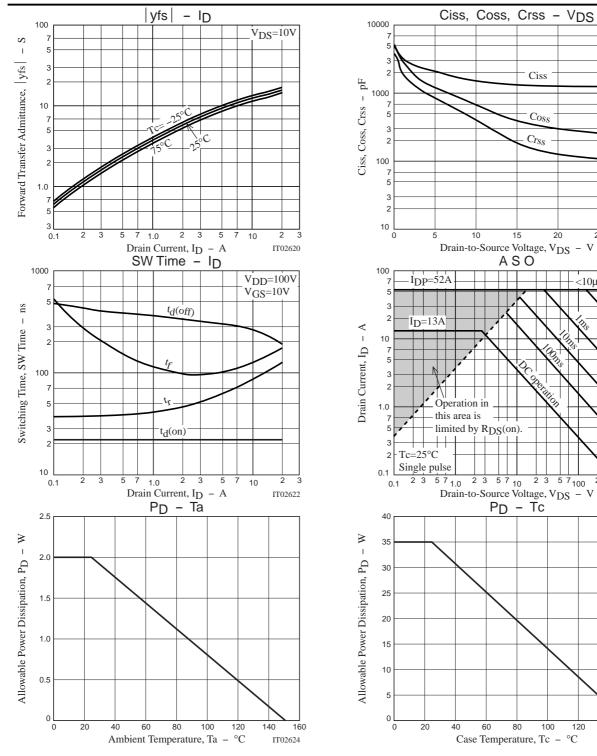
Marking : K2682

Switching Time Test Circuit





No.6783-2/4



f=1MHz

30

IT02621

100µs

5 71000

IT02623

2 3

120

140

160

IT02625

25

<10µs

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